

# c axis superfluid response of Copper-Oxide superconductors

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A novel interplay between  $d$ -wave superconducting order parameter symmetry and the underlying Cu  $3d$  orbital based electronic structure of Copper-Oxides leads to a striking anisotropy in the superfluid response of these systems. In clean tetragonal materials the  $c$ -axis penetration depth increases as  $T^5$  at low temperature  $T$ , in contrast to linear  $T$  behavior in the  $ab$ -plane. Disorder is a relevant perturbation which causes all components of the superfluid response to depend quadratically on temperature at low temperature. However, the cross-over temperature scale from the intrinsic  $d$ -wave behavior to the disorder dominated behavior for the in-plane response may be different from that for the out-plane response.

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A variety of experimental data on Copper-Oxide Superconductors are compatible with a pairing state of  $d_{x^2-y^2}$  symmetry in  $\text{CuO}_2$  planes. The existence of energy gap nodes in this state has profound consequences for the low temperature electro-magnetic response. The in plane penetration depth increases linearly with  $T$  at low  $T$  in contrast to the activated behavior of conventional superconductors. The linear- $T$  result holds in the regime where the response is governed by coherently propagating fermion quasi-particle excitations, i.e. at temperatures  $\Gamma \ll T \ll T_c$  where  $\Gamma$  is the superconducting quasiparticle scattering rate. Linear- $T$  behavior in the  $ab$ -plane has now been established in both chain and non-chain Copper-Oxides [1–4]. Experiment [1,2,4–6], however, indicates a much weaker  $T$  dependence of  $c$ -axis penetration depth. Straightforward extension of the  $d$ -wave model to 3D leads to line gap nodes on a warped cylindrical Fermi surface. This gives a linear- $T$   $c$ -axis response in apparent contradiction to experiment [7].

In this paper we propose that weak  $T$ -dependence of the  $c$ -axis superfluid density  $\rho_s^c$  is a general feature of non-chain cuprates with crystal tetragonal symmetry, whose origin lies in the simple but unusual electronic structure of these materials. Our analysis is based on the assumption that coherent Bloch bands along  $c$ -axis are present at low temperatures, i.e.  $k_z$  is a good quantum number. As discussed below, an essential feature of the electronic structure is that the  $c$ -axis hopping integral  $t_\perp(k_\parallel)$  is a function of the in plane momentum  $k_\parallel$  and is vanishingly small when  $k_\parallel$  lies along the zone diagonals of the 2D Brillouin zone [8,9]. The nodal lines of the  $d_{x^2-y^2}$ -wave gap  $\Delta(k_\parallel)$  and the zeros of  $t_\perp(k_\parallel)$  therefore coincide. This weakens the  $d$ -wave node contribution along the  $c$ -axis relative to the  $ab$ -plane and leads to a weak  $T$ -dependence of the  $c$ -axis superfluid response  $\rho_s^c$ . At sufficiently low temperatures disorder effects are always relevant, and tend to enhance the  $T$  dependence of  $\rho_s^c$ .

Let us first consider the electron structure in high- $T_c$  compounds with tetragonal symmetry. For simplicity we consider a tetragonal monolayer system, for example  $\text{HgBa}_2\text{CuO}_{4+\delta}$  [10]. LDA band structure calcu-

lations reveal that a minimal tight-binding model for high- $T_c$  compounds involves nearest-neighbour hopping between Cu  $3d_{x^2-y^2}$  and  $4s$  and O  $p_x$  and  $p_y$  orbitals [8,9]. Thus a model Hamiltonian for  $\text{HgBa}_2\text{CuO}_{4+\delta}$ , expressed in terms of bonding,  $\alpha_k = 2(\cos k_x p_x + \cos k_y p_y)/\omega_k$  where  $\omega_k = 2\sqrt{\cos^2 k_x + \cos^2 k_y}$ , and non-bonding,  $\beta_k = 2(\cos k_y p_x - \cos k_x p_y)/\omega_k$ , representation of orthogonal oxygen Wannier orbitals with respect to the Cu  $d_{x^2-y^2}$  orbital [11], is given by

$$H = \sum_k C_k^\dagger \begin{pmatrix} -E_d & 0 & t_{pd}\omega_k & 0 \\ 0 & E_s + 2t_{ss}d \cos k_z & t_{ps}\mu_k & t_{ps}z_k \\ t_{pd}\omega_k & t_{ps}\mu_k & 0 & 0 \\ 0 & t_{ps}z_k & 0 & 0 \end{pmatrix} C_k + \sum_i U n_{di}^2, \quad (1)$$

where  $C_k = (d_k, s_k, \alpha_k, \beta_k)$ ,  $(E_d, E_s)$  are the energy of  $(3d, 4s)$  orbital with respect to the O orbital, and  $(t_{pd}, t_{ps}, t_{ss})$  are wavefunction overlap integrals among  $d$ ,  $s$ , and  $p$  orbitals. The symmetry functions appearing here are  $\mu_k = 2(\cos k_x - \cos k_y)/\omega_k$  and  $z_k = 8 \cos k_x \cos k_y / \omega_k$ . The Hamiltonian (1) differs from that in Ref. [9] purely by retention of a strong Coulomb interaction  $U$  in the Cu  $d$  orbital. This produces a charge transfer insulator at half filling, a feature absent in LDA calculations.

In the strong coupling limit, the four band model (1) can be simplified as a one-band model by eliminating the highlylying Cu  $4s$  orbitals and the highlylying  $d-p$  spin triplets. This projection procedure can be carried out in two steps: firstly, by elimination of the highlylying  $4s$  orbital; and secondly, by solving the correlation problem within the unit cell and treating intercell hopping as a degeneracy lifting perturbation following Refs. [12,13]. This yields the well-known t-J model with both intra- and interlayer hoppings and exchanges. We assume the non-bonding orbitals are sufficiently lowlying that they are filled and inert. We notice that the dominant  $c$ -axis overlap is via large radius  $s$  orbitals [9]. Thus terms to second order in  $E_s^{-1}$  must be retained to describe effec-

tive  $c$ -axis hopping via O bonding orbitals. The lowest energy states within the  $\text{CuO}_2$  unit cell are spin 1/2 doublets  $|1\sigma\rangle$  with one hole per unit cell and Zhang-Rice singlets  $|2\rangle$  with two holes per unit cell. The  $ab$ -plane hopping matrix elements for Zhang-Rice singlets involve both  $d$ - $\alpha$  and effective  $\alpha$ - $\alpha$  overlap. However along the  $c$ -axis, the only channel for hopping is via the bonding O orbitals. It can be shown that the projected  $c$ -axis hopping integral has the form  $t_\perp(k_\parallel) = t_\perp^0 \mu_k^2$ , where  $t_\perp^0 = t_{ss}(t_{pd}t_{ps}M_0/E_dE_s)^2$  and  $M_0 = \langle 1\sigma|\alpha_\sigma^\dagger|2\rangle$  is the overlap of the state produced by eliminating the hole in the O bonding orbital and the ground state doublet. Thus  $t_\perp(k_\parallel)$  contains a  $k_\parallel$  dependent factor  $\mu_k^2$ , which vanishes when  $k_x = \pm k_y$  [14]. This is a robust feature of realistic strong correlation models of non-chain tetragonal materials and directly reflects the matrix element between Cu 4s and bonding O  $\alpha$  orbitals. It is worth pointing out that  $ab$ -plane anisotropy observed in  $c$ -axis magneto-transport experiments may be dominated by precisely this effect [15].

Now let us consider the effect of this  $k_\parallel$  dependent  $t_\perp$  on the  $c$ -axis superfluid response. For a clean system the electromagnetic response is governed by coherent 3D fermion quasiparticle excitations at low temperature. In this case the superfluid density (or inverse square of penetration depth) is given by [16]

$$\rho_s^\mu = \sum_k \left[ 2 \left( \frac{\partial \varepsilon_k}{\partial k_\mu} \right)^2 \frac{\partial f(\lambda_k)}{\partial \lambda_k} - \frac{\partial^2 \varepsilon_k}{\partial k_\mu^2} \frac{\varepsilon_k}{\lambda_k} \tanh(\beta \lambda_k / 2) \right], \quad (2)$$

where  $\varepsilon_k$  is the energy dispersion of electrons,  $\lambda_k = \sqrt{\varepsilon_k^2 + \Delta_k^2}$ , and  $f(\lambda_k)$  is the Fermi function. When  $t_\perp(k_\parallel) = t_\perp^0 \mu_k^2$  it is straightforward to show that at low temperature the  $c$ -axis superfluid response is

$$\rho_s^c(T) \sim \frac{3}{4} N(0) (t_\perp^0)^2 \left( 1 - \frac{5}{12} \left( \frac{\Delta(T)}{\Omega} \right)^2 - 450 \left( \frac{T}{\Delta_0} \right)^5 + o(T^5) \right), \quad (3)$$

where  $N(0)$  is the normal density of states on CuO planes,  $\Delta(T)$  is the energy gap,  $\Delta_0 = \Delta(0)$ , and  $\Omega$  is the energy cut off which is much larger than  $\Delta$ . The  $T^5$  term is from the first term in (2): one  $T$  is from the contribution of the linear density of states of the d-wave state and the other  $T^4$  is due to the  $(\cos k_x - \cos k_y)^4$  factor in  $t_\perp^2(k_\parallel)$ . The second term in (3) comes from the second term in (2), at low temperature it contributes a positive  $T^3$  term to  $\rho_s^c$  since the d-wave gap  $\Delta(T)/\Delta_0 \sim 1 - (T/\Delta_0)^3$ . However, the coefficient of this  $T^3$  term is proportional to  $(\Delta_0/\Omega)^2$ , which is extremely small. Therefore it is likely that the dominant temperature dependence of  $\rho_s^c$  should be  $T^5$  at low temperature. This  $T^5$  behavior in  $\rho_s^c$  is clearly very different from the  $t_\perp(k_\parallel) = \text{constant}$  case where  $\rho_s^c$  varies linearly with  $T$  at low temperature. In Fig. 1, we compare the temperature dependence of  $\rho_s^c(T)/\rho_s^c(0)$  in the whole temperature

regime for the above two cases. The temperature dependence of  $\rho_s(T)/\rho_s(0)$  along  $a$ -axis is also shown in Fig. (1) for comparison.

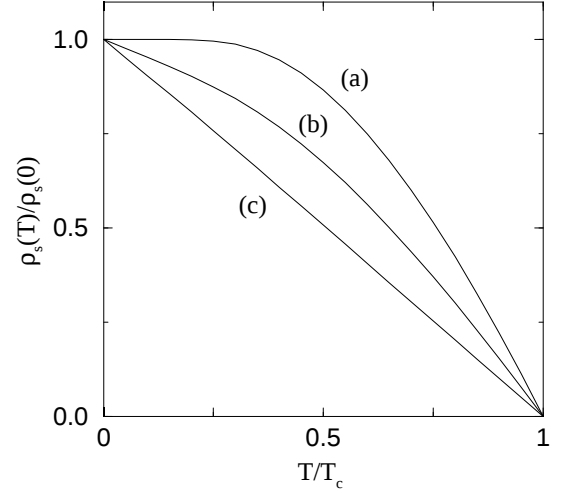


FIG. 1. Normalized superfluid density  $\rho_s(T)/\rho_s(0)$  vs  $T/T_c$ . The energy dispersion of electrons  $\varepsilon_k = -2t(\cos k_x + \cos k_y) - 4t' \cos k_x \cos k_y - 2t_\perp(k_\parallel) \cos k_z$  is used in the calculation. (a) is for the model with  $t_\perp(k_\parallel) = t_\perp^0 (\cos k_x - \cos k_y)^2/4$  along  $c$ -axis. (b) and (c) are for the model with  $t_\perp(k_\parallel) = t_\perp^0$  along  $c$ - and  $a$ -axis, respectively.  $t = 1$ ,  $t' = -0.25$ ,  $t_\perp^0 = 0.1$ ,  $T_c = 0.14$ , and the filling factor is 0.4. (The results are not sensitive to the change of parameters).

There are several effects which may lead to a finite hopping integral along the  $c$ -axis in the vicinity of the gap nodes in clean systems and thus a stronger  $T$  dependence of  $\rho_s^c$ . Many non-chain materials have some degree of orthorhombicity, i.e.  $t_x \neq t_y$ . Clearly this will affect the location of the gap nodes and the zeros of  $t_\perp(k_\parallel)$ . Following the previous treatment for the model (1), it can be shown that the projected  $c$ -axis hopping integral is still a function of  $k_\parallel$ , but  $t_\perp(k_\parallel)$  now has approximately the form  $t_\perp^0 (\cos k_x - \frac{t_y}{t_x} \cos k_y)^2/4$ . Thus the zeros of  $t_\perp(k_\parallel)$  are no longer on  $k_x = \pm k_y$  planes. The gap nodes may not lie on  $k_x = \pm k_y$  planes either, but there is no symmetry reason requiring the gap nodes to coincide to the zeros of  $t_\perp(k_\parallel)$ . Thus  $t_\perp$  is now finite at the gap node. Direct interplane O-O overlap can also lead to a finite dispersion around the gap nodes and eliminate the zeros in  $t_\perp(k_\parallel)$  altogether. In either case, we may model the  $c$ -axis electronic structure by  $t_\perp(k_\parallel) = t_\perp^0 \mu_k^2 + t_\perp^{\text{node}}$  with  $t_\perp^{\text{node}}$  the value of  $t_\perp$  at the gap nodes. Both effects are expected to be weak, but they generate a small linear term in  $\rho_s^c$ , with a slope proportional to  $(t_\perp^{\text{node}})^2$ , which dominates the  $c$ -axis superfluid response when  $T \ll t_\perp^{\text{node}}$ .

Sufficiently close to a nodal line the  $c$ -axis hopping rate always becomes small in comparison with the impurity

scattering rate, and thus disorder is always a relevant perturbation. Disorder introduces a finite quasiparticle lifetime and consequently a finite density of states at the Fermi level. At low temperature the correction to the superfluid density caused by finite quasiparticle scattering rates is approximately given by

$$\delta\rho_s^\mu \sim -\frac{2}{\pi} \sum_k \left( \frac{\partial \varepsilon_k}{\partial k_\mu} \right)^2 \int_{-\infty}^{\infty} d\omega f(\omega) \text{Im} \frac{(\omega + i\Gamma)^2 + \lambda_k^2}{[(\omega + i\Gamma)^2 - \lambda_k^2]^2}. \quad (4)$$

It can be shown that both the  $ab$  plane and the  $c$ -axis superfluid responses behave as  $T^2$  when  $T$  is much smaller than the quasiparticle scattering rate  $\Gamma$  [17]. However, the coefficients of the  $T^2$  terms are very different for the  $ab$  plane and the  $c$ -axis responses. On the  $ab$  plane,  $\rho_s^{ab}(T)/\rho_s^{ab}(0) \sim -(\Delta_0/\Gamma)(T/\Delta_0)^2$ ; while along the  $c$ -axis,  $\rho_s^c(T)/\rho_s^c(0) \sim -(\Gamma/\Delta_0)(T/\Delta_0)^2$ . Thus the  $T^2$  behavior of the  $c$ -axis response is by a factor  $(\Gamma/\Delta_0)^2$  weaker than that on the  $ab$  plane (generally  $\Gamma \ll \Delta_0$ ) due to the  $\mu_k^2$  factor in  $t_\perp(k_\parallel)$ . Notice that disorder has opposite effects in  $ab$  and  $c$ -axis; it weakens the  $T$ -dependence of the in-plane response and strengthens the  $T$ -dependence of the out of plane response.

Another important aspect of disorder is that it may disrupt the symmetry of bonding orbitals about the Copper site. The selection rule preventing hopping for momentum along  $k_x = \pm k_y$  is then relaxed. For example, consider the effect of interlayer defects on O site. This leads to a random component of  $t_\perp$  due to random variation in the matrix element  $M_0$  for a Zhang-Rice singlet discussed earlier. Near the gap nodes this fluctuating component in  $t_\perp$  dominates  $c$ -axis hopping, and thus electrons in the vicinity of nodes are well described by an impurity assisted hopping model which has been introduced in the literature on phenomenological grounds [7]. Impurity assisted hopping gives a new conduction channel and has a direct contribution to the  $c$ -axis superfluid density  $\rho_{s,imp}^c$ :

$$\rho_{s,imp}^c \sim \frac{4}{\beta} \sum_{\omega_n, k, k'} \langle \delta t_\perp(k) \delta t_\perp(-k) \rangle_{imp} \text{Tr} \left[ \sin^2 \frac{k_z}{2} G(k+k', \omega_n) G(k', \omega_n) - \cos^2 \frac{k_z}{2} G(k+k', \omega_n) \tau_3 G(k', \omega_n) \tau_3 \right]. \quad (5)$$

Thus the superfluid response induced by the impurity assisted hopping  $\rho_{s,imp}^c$  depends on the impurity average of the assisted hopping matrix element  $\langle \delta t_\perp(q) \delta t_\perp(-q) \rangle_{imp}$ . If the impurity scattering is isotropic in space, i.e.  $\langle \delta t_\perp(q) \delta t_\perp(-q) \rangle_{imp}$  is independent on  $q$ , then the assisted hopping contribution to  $\rho_s^c$  in a  $d$ -wave state is zero, resulted from the vanishing average of the  $d$ -wave gap on Fermi surface. If, however, the scattering is anisotropic, for example if  $\langle \delta t_\perp(q) \delta t_\perp(-q) \rangle_{imp}$  has the Lorentzian

form  $\langle \delta t_\perp(q) \delta t_\perp(-q) \rangle_{imp} = \frac{v_0^2 k_F \delta k}{(\mathbf{k}-\mathbf{k}')^2 + (\delta k)^2}$ , [7] then in the strong forward scattering limit ( $\delta k \rightarrow 0$ )  $\rho_{s,imp}^c$  behaves as  $T^2$  at low temperature:

$$\rho_{s,imp}^c \propto \Gamma_\perp \Delta N(0) \left[ 1 - 8 \ln 2 \left( \frac{T}{\Delta} \right)^2 + o(T^2) \right] \quad (6)$$

where  $\Gamma_\perp = 2\pi v_0^2 N(0)$ . For a finite  $\delta k$ ,  $\rho_{s,imp}^c$  behaves similarly to the  $\delta k \rightarrow 0$  case, but the overall amplitude of  $\rho_{s,imp}^c$  decreases with increasing  $\delta k$ .

The above discussion indicates that both the lifetime effect and the impurity assisted hopping contribute a  $T^2$  term to  $\rho_s^c$  at low temperature. The  $T^5$  behavior of  $\rho_s^c$  from the coherent tunneling of electrons is therefore observable only when  $T_c \gg T \gg \max(\Gamma, T^*)$ , where  $T^* \sim \frac{1}{2} [\Gamma_\perp \Delta_0 / (t_\perp^0)^2]^{1/3} T_c$  is a characteristic temperature above which the contribution from the coherent hopping of electrons to  $\rho_s^c$  is larger than that from the impurity assisted hopping. For a highly anisotropic and clean high- $T_c$  superconductor, generally  $\Gamma_\perp \ll t_\perp^0$  and  $t_\perp^0$  is smaller than or of the same order as  $\Delta_0$ . However, because of the 1/3 exponent in  $T^*$ ,  $T^*$  is a rather large temperature scale compared with even  $\Gamma$ . Thus assisted hopping may affect the  $c$ -axis superfluid response in a larger temperature region than the scattering lifetime effect.

Summarising the discussion above, we may draw a qualitative phase diagram for the temperature dependence of  $\rho_s^c$  and  $\rho_s^{ab}$  at low temperature: When  $T \ll \Gamma$ , the lifetime effect is important, both  $\rho^{ab}$  and  $\rho_s^c$  vary quadratically with  $T$ . When  $T^* \gg T \gg \Gamma$ , the impurity assisted hopping becomes more important to the  $c$ -axis superfluid response. In this case,  $\rho_s^c$  varies still quadratically with  $T$ , but the coefficient of the  $T^2$  term in  $\rho_s^c(T)/\rho_s^c(0)$  is proportional to  $\Gamma_\perp / (t_\perp^0)^2 \Delta$ , which is generally smaller than that in the  $T \ll \Gamma$  case where the coefficient of  $T^2$  term in  $\rho_s^c(T)/\rho_s^c(0)$  is proportional to  $\Gamma/\Delta^3$ . When  $T_c \gg T \gg \Gamma$  for  $\rho_s^{ab}$  or  $T_c \gg T \gg T^*$  for  $\rho_s^c$ , the disorder effect is not so important and the temperature dependences of  $\rho_s^c$  and  $\rho_s^{ab}$  in a clean system should be recovered. Thus there is a crossover from  $T^2$  to  $T$  when  $T \sim \Gamma$  for  $\rho_s^{ab}$  and from  $T^2$  to  $T^5$  when  $T \sim T^*$  for  $\rho_s^c$  as  $T$  increases at low temperature [18]. A simple formula which gives a qualitative measure for the crossover of  $\rho_s^c$  from the intrinsic  $T^5$  behavior to the disorder  $T^2$  behavior is  $\rho_s^c(T) \approx \rho_s^c(0) + \alpha T^2 [1 + (T/T^*)^3]$  with  $\alpha$  a scattering potential dependent constant. The above picture may be also valid for the case of substitutional impurities such as Zn, but we cannot rule out a possible formation of a ‘‘impurity band’’ which may have a stronger effect on the low temperature behavior of  $\rho_s^c$  than the disorder effects previously discussed.

In comparing the predictions of this model to experiment for a given system, it is essential to assess whether coherent Bloch band are present at all. The answer to this question in the normal state of highly anisotropic copper-oxides, such as BSSCO, appears to be no. The  $c$ -axis mean free path is generally very short compared

with the  $c$ -axis lattice constant. Microwave [19] and thermal Hall measurements [20], however, reveal that the mean free path grows very rapidly in the superconducting state. The superconducting quasiparticle scattering rate is therefore much lower than the extrapolated normal state scattering rate. Thus it is our belief that the available experimental data favor coherent Bloch band formation along  $c$ -axis at low temperature below  $T_c$ . For BSSCO,  $t_{\perp}^0$  is small and  $\rho_s^c$  might be dominated by the impurity assisted hopping [7]. However, for other compounds with lattice tetragonal symmetry and relatively lower anisotropy, such as LaSrCuO, TlBaCaCuO and Hg-BaCuO, we believe that the coherent band should have substantial contribution to  $\rho_s^c$ . Experimentally, a crucial test for this can be done by carefully measuring and analysing  $\rho_s^c$  data in these compounds to see if the predicted  $T^5$  behavior exists. (The  $T^5$  behavior in  $\rho_s^c$  is not applicable to YBCO as it has CuO chain layers and non-flat CuO planes [21].)

In conclusion, we have demonstrated that there exists a remarkable interplay between underlying electronic structure and orbital parameter symmetry in Copper-Oxides. The  $c$ -axis electromagnetic response reflects not only the symmetry of the order parameter but also the relative symmetry of the Copper orbitals involved in  $c$ -axis and  $ab$ -plane conduction. At low temperature the disorder effect dominates and both  $\rho_s^c$  and  $\rho_s^{ab}$  have  $T^2$  dependence. Above some characteristic temperatures, which may be different for  $\rho_s^c$  and  $\rho_s^{ab}$ , the temperature dependences in a clean system, linear  $T$  for  $\rho_s^{ab}$  and  $T^5$  for  $\rho_s^c$ , are expected.

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